

DESCRIPTION

SYNTHETIC SILICA GLASS MEMBER, PHOTOLITHOGRAPHY

APPARATUS

AND PROCESS FOR PRODUCING PHOTOLITHOGRAPHY APPARATUS

5 **Technical Field**

The present invention relates to a synthetic silica glass member, to a photolithography apparatus and to a process for producing the photolithography apparatus. More specifically, it relates to a
10 synthetic silica glass member for a photolithography apparatus used in an optical system with lenses, mirrors and the like for photolithography technology, in a specific wavelength range of no greater than 400 nm and preferably no greater than 300 nm, to a
15 photolithography apparatus constructed using such optical members and to a process for producing the photolithography apparatus.

Background Art

Photolithography apparatuses known as "steppers"
20 (projection exposure apparatuses) are conventionally used for photolithography techniques which accomplish exposure and transfer of intricate patterns of integrated circuits onto wafers of silicon or the like. The optical system of a stepper is constructed with an
25 illumination optical system which uniformly irradiates light from a light source onto a reticle and a

projection optical system which projects and transfers the integrated circuit pattern formed on the reticle onto a wafer at a 1/5 reduction, for example.

Recent higher integration of LSIs has required even shorter wavelengths for photolithography apparatus light sources, from g rays (436 nm) to i rays (365 nm) or even KrF (248.3 nm) or ArF (193.4 nm) excimer lasers. There has also been a corresponding demand for photolithography apparatuses allowing exposure with even finer minimum workability beam width. However, when the light source emits light with a wavelength range in the ultraviolet region, and particularly in the region below 250 nm, the light transmittance is too poor for practical use when employing lens materials used in illumination optical systems and projection optical systems designed for light with a longer wavelength region than i rays. Lens materials used in illumination optical systems and projection optical systems are therefore limited to silica glass and some crystal materials that exhibit high light transmittance.

When a silica glass member is used in the optical system of a photolithography apparatus, extremely high quality is required for exposure of the integrated circuit pattern with a large area at high resolution. For example, for a member with a relatively large diameter of about 200 mm, the refractive index

distribution of the member must be on the order of no greater than 10^{-6} . It is also necessary to reduce the birefringence, i.e. minimize internal strain of the member, and this improves the uniformity of the refractive index distribution and is also important for the resolution of the optical system. Consequently, there have been strict limitations on silica glass members made of silica glass alone that can be used for photolithography apparatuses employing ultraviolet light from an excimer laser stepper as the light source.

In addition, silica glass members used for photolithography apparatuses using ultraviolet light as the light source must have high transmittance (small loss factor) in addition to the aforementioned conditions. This is because a very large number of lenses are provided in the illumination optical system or projection optical system of a photolithography apparatus to compensate for aberration, and the optical loss of each individual lens can lead to reduced transmittance of the apparatus as a whole.

Silica glass includes fused silica glass obtained by melting natural crystal powder and synthetic silica glass obtained by chemical synthesis, but synthetic silica glass is characterized by being of high purity with low metal impurities, and having high transmittance for ultraviolet light of a wavelength of

250 nm or smaller. Homogeneous synthetic silica glass with a large aperture can also be produced due to the nature of the production process.

Disclosure of the Invention

5 Even with synthetic silica glass, however, the action of a high power ultraviolet beam or excimer laser beam produces a 260 nm absorption band due to structural defects known as NBOHCs (Non-Bridging Oxygen Hole Centers, having the structure $\equiv\text{Si}-\text{O}\cdot$) or a 215 nm
10 absorption band due to structural defects known as E' centers (having the structure $\equiv\text{Si}\cdot$, where $\equiv$ is not a triple bond but represents bonding to 3 oxygen atoms, and $\cdot$ represents an unpaired electron), and transmittance in the ultraviolet region is
15 significantly reduced as a result. Because the center wavelengths of these absorption bands are close to the oscillation wavelength of the KrF excimer laser or ArF excimer laser used as the light source of the stepper, the transmittance of the optical system is considerably
20 reduced by light absorption. A large 215 nm absorption band is also sometimes produced even with low total ultraviolet beam irradiation (= low irradiation energy or a short irradiation time). Since the absorption band is usually produced at the initial stage of
25 irradiation of an excimer laser, the absorption is referred to as initial irradiation absorption. Thus,

not all synthetic silica glass can necessarily be used
for lens members of such apparatuses, and therefore
synthetic silica glass with low initial irradiation
absorption is necessary in order to satisfactorily
5 guarantee practical performance for the apparatus.

To date it has been independently confirmed that
the desired properties for an optical member used in a
photolithography apparatus employing an ArF excimer
laser or the like with a wavelength of 200 nm or less
10 as the light source are a low loss factor before
irradiation with an ArF excimer laser beam (wavelength:
193.4 nm) and low transmittance reduction even with
prolonged irradiation with an ArF excimer laser (i.e.
low prolonged transmittance variation); however, it has
15 been difficult to obtain silica glass members
satisfying both of these properties, and therefore no
photolithography apparatus has existed with an ArF
excimer laser employing such a member as the light
source.

20 It is an object of the present invention, which
has been accomplished in light of these problems, to
provide a synthetic silica glass member which can
increase the transmittance of a photolithography
apparatus employing an ArF excimer laser as the light
25 source and thereby exhibit adequate properties for
practical use, as well as a high-resolution

photolithography apparatus employing it and a process for its production.

The present inventors investigated the relationship between the properties of silica glass and the degree of the initial irradiation absorption in order to elucidate the cause of the initial irradiation absorption of silica glass for ultraviolet light. As a result, it was found that when silica glass is synthesized in a reducing atmosphere for doping of hydrogen in order to achieve enhanced durability, providing an atmosphere that is more strongly reducing than necessary results in silica glass containing a high degree of the structural defect $\equiv\text{Si-H}$ (which is easily cleaved by ultraviolet irradiation with low energy density to become an E' center) which is a cause of lower transmittance of the silica glass member, or in other words, that silica glass with a greater hydrogen molecule concentration tends to exhibit high initial irradiation absorption. It was found at the same time that silica glass containing virtually no hydrogen molecules exhibits reduced transmittance with prolonged irradiation with an ArF excimer laser.

Thus, the synthetic silica glass of the invention is a synthetic silica glass member used in a photolithography apparatus employing light in a wavelength range of 400 nm or less, wherein hydrogen

molecules are present at a certain level and the $\equiv\text{Si-H}$ concentration is lowered during synthesis by appropriately adjusting the hydrogen molecule concentration of the silica glass during synthesis in a reducing atmosphere, the member being characterized in that, upon 1×10^4 pulse irradiation with an excimer laser at an energy density from $0.1 \mu\text{J}/\text{cm}^2 \cdot \text{p}$ to $200 \text{ mJ}/\text{cm}^2 \cdot \text{p}$, the loss factor at 193.4 nm measured after irradiation (i.e. the initial irradiation absorption) is no greater than 0.0050 cm^{-1} , the hydrogen molecule concentration is from $1 \times 10^{16} \text{ molecules}/\text{cm}^3$ to $2 \times 10^{18} \text{ molecules}/\text{cm}^3$ and the loss factor before ultraviolet irradiation is no greater than 0.0020 cm^{-1} .

The photolithography apparatus of the invention is a photolithography apparatus comprising an exposure light source that emits light with a wavelength of 400 nm or less as the exposure light, a reticle with a pattern image formed therein, an illumination optical system that irradiates light outputted from the exposure light source onto the reticle, a projection optical system that projects the pattern image outputted from the reticle onto a photosensitive plate and an alignment system that positions the reticle and the photosensitive plate, wherein at least some of the synthetic silica glass members composing the illumination optical system, the synthetic silica glass

members composing the projection optical system and the reticle (for example, the collimator lens, flyeye lens, condenser lens, projection lens, etc. in the described embodiment) consist of synthetic silica glass members characterized as described above.

By constructing all or some of the optical members of a photolithography apparatus (for example, the stepper 1 in the described embodiment) using synthetic silica glass members according to the invention, it is possible to ensure high transmittance and adequate properties for practical use even when the light source is an ArF excimer laser. The synthetic silica glass member has a hydrogen molecule concentration of 1×10^{16} molecules/cm³ to 2×10^{18} molecules/cm³ and a loss factor of no greater than 0.0020 cm⁻¹ before ultraviolet irradiation.

A hydrogen molecule concentration of less than 1×10^{16} molecules/cm³ results in greater reduction in transmittance with prolonged irradiation with an ArF excimer laser. On the other hand, synthesis under conditions with a hydrogen molecule concentration of greater than 2×10^{18} molecules/cm³ tends to result in a higher ≡Si-H concentration as well and greater initial irradiation absorption, and a non-uniform hydrogen molecule concentration in the silica glass.

A photolithography apparatus constructed using a

synthetic silica glass member with a loss factor of greater than 0.0020 cm^{-1} before ultraviolet irradiation has low transmittance (throughput) for the optical system as a whole, and lower resolution is exhibited due to heating of the member upon irradiation with the laser or changes in the surface shape. In the case of a synthetic silica glass member with a loss factor (initial irradiation absorption) exceeding 0.0050 cm^{-1} at 193.4 nm measured after irradiation with 1×10^4 pulse irradiation at an energy density of $0.1 \text{ } \mu\text{J}/\text{cm}^2 \cdot \text{p}$ to $200 \text{ mJ}/\text{cm}^2 \cdot \text{p}$, a large variation in transmittance is exhibited when the laser is switched on or off, and therefore the photolithography apparatus employing it has a large light exposure variation.

The process for producing the photolithography apparatus of the invention comprises an ingot synthesizing step in which a synthetic silica glass ingot with a hydrogen molecule concentration of from $1 \times 10^{16} \text{ molecules}/\text{cm}^3$ to $2 \times 10^{18} \text{ molecules}/\text{cm}^3$ is synthesized; an ingot cutting step in which the synthetic silica glass ingot is cut to obtain a synthetic silica glass member of the prescribed shape and size; a loss factor measuring step for measurement of the loss factor of the synthetic silica glass member before ultraviolet irradiation and the loss factor at 193.4 nm after irradiation with an ArF excimer laser

with 1×10^4 pulse irradiation at an energy density
from $0.1 \mu\text{J}/\text{cm}^2 \cdot \text{p}$ to $200 \text{ mJ}/\text{cm}^2 \cdot \text{p}$, to obtain a
synthetic silica glass member with a loss factor of no
greater than 0.0020 cm^{-1} before ultraviolet irradiation
5 and a loss factor of no greater than 0.0050 cm^{-1} at
193.4 nm; and an optical system constructing step in
which the synthetic silica glass member obtained in the
loss factor measuring step is used to construct at
least some of the synthetic silica glass members
10 composing the illumination optical system, the
synthetic silica glass members composing the projection
optical system and the reticle.

According to this production process, it is
possible to obtain a high-resolution photolithography
15 apparatus employing a synthetic silica glass member
with a loss factor of no greater than 0.0020 cm^{-1}
before ultraviolet irradiation and a loss factor of no
greater than 0.0050 cm^{-1} at 193.4 nm.

According to the invention, the distribution range
20 (variation width) is preferably small for the hydrogen
molecule concentration value in the radial direction at
any given point of the synthetic silica glass member.
The radial direction is the direction along any desired
plane in the member perpendicular to the direction of
25 the incident irradiated beam. Specifically, for the
hydrogen molecule concentration at the center of the

member (geometrical center of gravity), the variation width V of the hydrogen molecule concentration at any desired point on the plane including this center preferably satisfies the condition represented by $-50\% \leq V \leq +50\%$, and more preferably satisfies the condition represented by $-20\% \leq V \leq +20\%$. Thus, with a small distribution range (variation width) for the hydrogen molecule concentration in the radial direction of the member, it is possible to achieve a stable exposure dose over a prolonged period without irregularity in the degree of reduction in transmittance at any point in the member in the radial direction of the member, even when the ArF excimer laser is irradiated thereon for a prolonged period.

As explained above, when the hydrogen molecule concentration exceeds 2×10^{18} molecules/cm³ the variation width of the hydrogen molecule concentration tends to be larger. In order to reduce the variation of the hydrogen molecule concentration, it is preferred to adjust the oxygen gas/hydrogen gas flow ratio to 0.25-0.40 for the total combustion gas (oxygen-containing gas and hydrogen-containing gas) ejected from the burner during the silica glass ingot synthesis step. If the flow ratio is within this range it will be possible to include the necessary number of hydrogen molecules in the silica glass to prevent reduced

transmittance during prolonged irradiation of light,
while also minimizing the degree of $\equiv\text{Si-H}$ structure
which is a cause of initial irradiation absorption, and
to thereby reduce the variation width for the hydrogen
5 molecule concentration; in addition, since the various
conditions for the ingot synthesis step such as the
synthesis burner shape, the raw material flow, the
oscillating pattern of the target holding the ingot,
etc., are also factors determining the hydrogen
10 molecule concentration in the ingot and its variation
width, the $\equiv\text{Si-H}$ concentration, etc., appropriate
adjustment of these conditions is preferred. For
example, if the raw material flow is too high the
center temperature of the flame falls, tending to
15 result in easier hydrogen concentration distribution.

Brief Description of the Drawings

Fig. 1 is a general structural diagram showing an
embodiment of the construction of a photolithography
apparatus according to the invention.

20 Fig. 2 is a general cross-sectional view showing
an embodiment of a production apparatus for synthetic
silica glass according to the invention.

Fig. 3 is a schematic view of the burner of the
production apparatus shown in Fig. 2 as seen from the
25 exhaust nozzle side.

Fig. 4 is a flow chart showing the procedure for a

transmittance measuring method.

Fig. 5 is a general structural diagram of a spectrophotometer used for transmittance measurement.

Fig. 6 is a graph showing an example of change in the transmittance of a calibration sample with time after completion of cleaning.

Fig. 7 is a general structural diagram of a correcting transmittance measuring apparatus used for calculation of the correction value K_L .

Fig. 8 is a graph showing an example of the sample thickness dependency of loss of a correction sample.

Fig. 9 is a graph showing variation in the loss factor with respect to the irradiation pulse number for samples corresponding to Example 5 and Comparative Example 1.

Fig. 10 is a graph showing variation in the loss factor with respect to the irradiation pulse number for samples corresponding to Example 8 and Comparative Example 3.

Best Mode for Carrying Out the Invention

A preferred embodiment of the present invention will now be explained with reference to the attached drawings. Fig. 1 is a general structural diagram showing an embodiment of a photolithography apparatus (stepper 1) according to the invention. In Fig. 1, the Z direction is the direction parallel to the optical

axis of the projection optical system 370, the Y direction is the direction in the plane of the paper and perpendicular to the Z direction, and the X direction is the direction perpendicular to the paper surface and the Z direction.

The stepper 1 shown in Fig. 1 is constructed with an exposure light source 310 that emits light primarily with a wavelength of 400 nm or less as the exposure light, a reticle R with a pattern image formed therein, an illumination optical system 320 that irradiates light outputted from the exposure light source 310 onto the reticle R, a projection optical system 370 that projects the pattern image outputted from the reticle R onto a wafer (photosensitive plate) W at a reduction of 1/4 or 1/5 and an alignment system 322 that positions the reticle R and the wafer W. Also, at least some of the synthetic silica glass members composing the illumination optical system 320 (for example, the collimator lens, flyeye lens, condenser lens, etc.), the synthetic silica glass members composing the projection optical system 370 (for example, reducing projection lens, etc.) and the reticle R consist of synthetic silica glass members according to the invention.

In other words, all or some of the synthetic silica glass members (including other lens and mirror

members not shown here) such as the collimator lens, flyeye lens, condenser lens, projection lens, etc. are characterized in that upon 1×10^4 pulse irradiation at an energy density from $0.1 \mu\text{J}/\text{cm}^2 \cdot \text{p}$ to $200 \text{ mJ}/\text{cm}^2 \cdot \text{p}$,
5 the loss factor at 193.4 nm measured after irradiation is no greater than 0.0050 cm^{-1} .

A synthetic silica glass member characterized in such a manner is obtained from a material with a hydrogen molecule concentration from 1×10^{16}
10 molecules/ cm^3 to 2×10^{18} molecules/ cm^3 and a loss factor before ultraviolet irradiation of no greater than 0.0020 cm^{-1} (see the examples and comparative examples which follow).

The wafer W is placed on a leveling stage (not
15 shown) and the leveling stage is situated on a Z stage 382 which is finely adjustable in the optical axis direction (Z direction) of the projection optical system by a driving motor 386. The Z stage 382 is placed on an XY stage 384 which can move in the two-
20 dimensional (XY) direction in a step-and-repeat system driven by a driving motor 388. The reticle R is placed on a reticle stage 330 which is movable in two dimensions within the horizontal plane.

The exposure beam emitted from the exposure light
25 source 310 is directed parallel to a collimator lens (not shown) in the illumination optical system 320 and

the beam intensity is rendered uniform by a flyeye lens (not shown), after which it is condensed by a condenser lens (not shown) and reaches the reticle R. The light that has passed through the reticle R is condensed by a projection lens (not shown) in the projection optical system 370 and reaches the wafer W, and this reduces the integrated circuit pattern formed on the reticle R for exposure of the wafer W.

The exposure beam from the exposure light source 310 thus uniformly irradiates the pattern formed on the reticle R through the illumination optical system 320, so that the pattern image of the reticle R is transferred by exposure onto the shot area of the wafer W by the projection optical system 370. The exposure beam may be an exposure beam with a wavelength of 248 nm (KrF excimer laser), 193 nm (ArF excimer laser) or 157 nm (F₂ laser).

Upon completion of transfer exposure of the reticle R pattern onto one shot area of the wafer W, the XY stage 384 is moved by stepping so that the next shot area of the wafer W is aligned with the exposure region of the projection optical system 370. The two-dimensional position of the leveling stage on which the wafer W is placed is constantly monitored at a resolution of about 0.01 μ m, for example, by measurement of the distance from a mobile mirror 389

anchored on the leveling stage using an interferometer (not shown), and the output of the laser interferometer is fed to the stage control system 350.

5 The reticle R is positioned on the reticle stage 330 so that the center of the transfer pattern on the reticle R is aligned with the optical axis AX of the projection optical system. The positioning of the reticle R is accomplished using a plurality of reticle alignment marks (reticle marks) provided near the outer
10 periphery of the reticle R. Two types of reticle marks are provided: reticle marks for positioning in the X direction and reticle marks for positioning in the Y direction. The alignment system 322 uses an exposure beam extracted by splitting part of the exposure beam
15 from the exposure light source 310 as a reference beam (alignment beam). The alignment system 322 provides one beam at the position of each reticle alignment mark.

20 The reference beams that have passed through the illumination optical system 320 are incident to the reticle marks provided outside the pattern area of the reticle R. The reticle marks consist of, for example, triangular transparent windows formed on non-transparent sections surrounding the pattern. When an alignment beam is reflected at the reticle mark section
25 it reenters the alignment system 322. The portion of the alignment beam that has passed through the reticle

mark passes through the projection optical system 370 and is incident onto substrate alignment marks (wafer marks) formed around each shot area on the wafer W. The wafer marks need not be provided surrounding each shot area but may be provided only at prescribed positions of the wafer, for example, on the peripheral region of the wafer. Two types of wafer marks are also provided: wafer marks for positioning in the X direction and wafer marks for positioning in the Y direction, corresponding to the reticle marks. Reflected light from the wafer marks takes the opposite path from the incident light, and it reenters the alignment system 322 through the projection optical system 370 and the reticle marks.

Thus, the alignment system 322 detects the relative positioning of the reticle R and the wafer W by inputted reflection of the alignment beam from the reticle R and wafer W. The output from the alignment system 322 is supplied to the main control system 360. Then, by supplying the output from the main control system 360 to a reticle exchange system 340 and stage control system 350, it is possible to adjust the spatial positioning of the reticle R and wafer W. As a result, it is possible to maintain high superposition precision between the pattern formed on each shot area of the wafer W and the pattern image of the reticle R

which is transferred by exposure. The illumination optical system 320 uniformly illuminates the reticle R in a slit shape as the object of irradiation. The projection optical system 370 is situated between the surface P1 of the reticle R and the surface P2 of the wafer W.

By thus providing a projection optical system 370, illumination optical system 320 and/or reticle R composed of optical glass members according to the invention, it is possible to obtain a stepper 1 with low exposure light variation and high resolution.

A process for producing a photolithography apparatus according to the invention will now be explained. As mentioned above, the process for producing a photolithography apparatus according to the invention mainly comprises an ingot synthesizing step, an ingot cutting step, a loss factor measuring step and an optical system constructing step.

First, the ingot synthesizing step will be explained. In the ingot synthesizing step there is synthesized a synthetic silica glass ingot with a hydrogen molecule concentration of 1×10^{16} molecules/cm³ to 2×10^{18} molecules/cm³. Fig. 2 shows an embodiment of a production apparatus for a synthetic silica glass ingot from which a synthetic silica glass member of the invention is prepared. As shown in Fig.

2, this synthetic silica glass production apparatus 50 comprises a furnace 60, a burner 70 situated at the top of the furnace 60, and a target 80 provided below the burner 70 in the furnace space 64 formed inside the furnace 60.

The furnace 60 is constructed with a refractory body 63 inside a furnace frame 62 provided on a hearth plate 61, and the burner 70 is provided through the top of the furnace frame 62 and refractory body 63. The burner 70 has a multitube structure which will be explained later, and its expelling end 70a is directed downward into the furnace space 64. The target 80 is composed of a plurality of non-transparent silica glass plates stacked one upon the other, with the uppermost surface set on the top side of a horizontal disk 82 provided on a vertically extending support rod 81, facing the expelling end 70a of the burner 70. In the furnace frame 62 there is formed an discharge outlet 65 whereby exhaust gas such as HCl which is generated in the furnace 60 during synthesis of the silica glass is discharged out of the furnace 60, and a discharge conduit 66 in communication with the outside air is connected to the discharge outlet 65. A window 67 is provided in the outer wall of the furnace 60 to allow observation of the furnace space 64.

Fig. 3 shows the burner 70 from an angle facing

the expelling end 70a, and a raw material expelling tube 71, oxygen/hydrogen expelling tubes 72,73 an oxygen expelling tube 74 and a hydrogen expelling tube 75 are provided in that order from the center. The raw material expelling tube 71 is positioned at the center of the burner 70, and a silicon compound such as silicon tetrachloride (SiCl_4) as the raw material and a carrier gas (normally oxygen gas) for dilution are discharged from the inner space 71a. The two oxygen/hydrogen expelling tubes 72,73 are arranged concentrically surrounding the raw material expelling tube 71, and combustion gases including oxygen gas and hydrogen gas are discharged from the respective inner spaces 72a,73a. The plurality of oxygen expelling tubes 74 are positioned outside of the oxygen/hydrogen expelling tube 73, and oxygen is discharged from their respective inner spaces 74a. A hydrogen discharge tube 75 is positioned concentrically with the raw material expelling tube 71 and the oxygen/hydrogen expelling tubes 72,73 in a manner surrounding the oxygen expelling tubes 74, and hydrogen gas is discharged from its inner space 75a. The oxygen gas and hydrogen gas are discharged through separate expelling tubes in this manner so that the gases react uniformly during the silica glass synthesis.

The silica glass synthesis is accomplished by

expelling the raw material, oxygen and hydrogen from the burner 70 toward the top surface of the target 80 while burning them. This causes the silicon tetrachloride to react with the oxygen and hydrogen (hydrolysis), and the synthesized silica glass powder accumulates on the target 80 and vitrifies to form a synthetic silica glass ingot IG. For an overall uniform composition of the produced ingot IG, the support rod 81 is driven to rotate the target 80 at a prescribed speed in the axial direction while vibrating at a prescribed time interval in the horizontal direction. Also, the entire target 80 is pulled downward at a prescribed speed during production in order to constantly maintain a fixed distance between the top end of the ingot IG and the expelling end 70a of the burner 70.

A synthetic silica glass ingot is produced in this manner, and since hydrogen molecules are introduced during the synthesis and are released during heat treatment, the hydrogen molecule concentration of the produced synthetic silica glass can be controlled by the synthesis conditions (for example, the proportion of oxygen gas and hydrogen gas supplied from the burner 70) and the heat treatment conditions (for example, conducting or not conducting a heat treatment step). The various conditions are therefore modified so that

the ingot has a hydrogen molecule concentration of 1×10^{16} molecules/cm³ to 2×10^{18} molecules/cm³. The hydrogen molecule concentration of the resulting synthetic silica glass ingot can be confirmed by Raman spectroscopy or the like.

Once the synthetic silica glass ingot with the prescribed hydrogen molecule concentration has been obtained in this manner, the synthetic silica glass ingot is subjected to heat treatment before being conveyed to the ingot cutting step described later. As an example of such heat treatment there may be mentioned a step of holding the produced ingot at a fixed temperature for a prescribed period of time and then lowering the temperature at a prescribed temperature-lowering rate and allowing it to cool.

The ingot cutting step will now be explained. The ingot cutting step is a step in which, after the aforementioned heat treatment, the synthetic silica glass ingot is cut to obtain a synthetic silica glass member with the prescribed shape and size. First, a lump of a size corresponding to the size of the synthetic silica glass member to be fabricated is cut out from the ingot and subjected to grinding. It is then finely polished with SiO₂ or the like for finishing into a synthetic silica glass member with the prescribed dimensions.

Once the synthetic silica glass member with the prescribed dimensions and the prescribed composition (hydrogen molecule concentration of 1×10^{16} molecules/cm³ to 2×10^{18} molecules/cm³) is obtained in this manner, it is conveyed to the loss factor measuring step.

In the loss factor measuring step, the lost factor is first measured before ultraviolet irradiation. The portion with a loss factor of no greater than 0.0020 cm⁻¹ before ultraviolet irradiation is extracted from the synthetic silica glass member with the aforementioned hydrogen molecule concentration.

An example of a method of measuring the loss factor of a synthetic silica glass member before ultraviolet irradiation will now be explained. This explanation will concern a case of measuring the transmittance of an evaluation sample M (thickness L_0) composed of an optical member for ultraviolet use, using a commercially available spectrophotometer.

The transmittance measuring method used here, as shown in Fig. 4, comprises the following procedure: a first step of cleaning the evaluation sample M (including a drying step) (S1), a second step of measuring the transmittance within a prescribed time period and determining the transmittance T (S2), a third step of calibrating the obtained transmittance T

to the transmittance T_c for the evaluation time t_c (S3) and a fourth step of correcting the transmittance T_c for the evaluation time to the true transmittance T_o (S4). This procedure requires determining in advance the transmittance reduction rate $[a]$ and critical elapsed time $[t_m]$ corresponding to the material and thickness ($= L_o$) of the evaluation sample M , as well as the correction value K_L for the spectrophotometer.

First, the spectrophotometer used for the transmittance measurement will be explained. Fig. 5 shows an example of a construction of a commercially available spectrophotometer. For measurement of the transmittance of an object 111 using the spectrophotometer 110, the object 111 is placed between a mirror 125 and a mirror 126 and irradiated with a beam (ultraviolet light) from a light source 112. The beam from the light source 112 enters a mirror 121 through a slit 141. The beam reflected at the mirror 121 passes through a slit 142 and enters a diffraction grating 131 through a mirror 122. The primary diffraction beam 123 is reflected by a mirror 123 and enters a mirror 124 through a slit 143. The beam reflected by the mirror 124 then enters a mirror 125 or a mirror 127 through a chopper mirror 113. The beam (measuring beam) reflected by the mirror 125 enters the object 111. The beam (transmitted beam) that has

passed through the object 111 enters a detector 114 by way of a mirror 126. Meanwhile, the beam (reference beam) reflected by the mirror 127 enters the detector by way of mirrors 128,129. The transmitted beam and
5 reference beam received by the detector 114 are separated by a processor 115 and the transmitted beam intensity I and reference beam intensity I_0 are determined. The ratio I/I_0 is used to calculate the transmittance of the object 111. All the members of
10 the apparatus except for the processor 115 are covered by a sealed chamber 116 which is nitrogen purged during the transmittance measurement.

The procedure for determining the parameters of the transmittance reduction rate $[a]$ and critical
15 elapsed time $[t_m]$ corresponding to the material and thickness $(= L_0)$ of the evaluation sample M will now be explained. First, a calibration sample is prepared of the same material as the evaluation sample M and with the same thickness $(= L_0)$. It is then cleaned (and
20 dried), after which the procedure of measuring the transmittance using the spectrophotometer 110 is repeated a plurality of times while changing the elapsed time for the transmittance measurement (time elapsed after completion of cleaning). The results are
25 then plotted on a coordinate graph with elapsed time on the horizontal axis and transmittance on the vertical

axis, to prepare a first plot graph.

The first plot graph obtained in this manner represents the change in transmittance with time for the calibration sample, and the plot sequence can be fitted to a line from completion of cleaning to a given time (as shown in Fig. 6, for example). The line declines gradually as the elapsed time increases (i.e. it has a negative slope). The slope is calculated as the transmittance reduction rate $[a]$ (%/min), while the critical elapsed time that can be fitted to the line is read as the critical elapsed time $[t_m]$ (minutes). The transmittance reduction rate $[a]$ and critical elapsed time $[t_m]$ for the evaluation sample M are determined in this manner.

Thus, the values for the transmittance reduction rate $[a]$ and critical elapsed time $[t_m]$ obtained for the calibration sample can be treated as those for the evaluation sample because the parameters for the transmittance reduction rate $[a]$ and critical elapsed time $[t_m]$ are the same if the sample material and thickness are equivalent. Consequently, if the transmittance is measured for the evaluation sample M within a prescribed time period during which a constant rate of reduction in transmittance is maintained (corresponding to the period from completion of cleaning to elapse of the critical elapsed time $[t_m]$)

in order to determine the transmittance T for the elapsed time t ($< t_m$), then this transmittance T can be calibrated by converting it to the transmittance T_c for an arbitrarily selected evaluation time t_c ($< t_m$) within the aforementioned prescribed time period, using the following formula (1).

$$T_c = T + (t - t_c) \times [a] \quad (1)$$

In formula (1), the transmittance T_c is the transmittance expected if measured for the reference time t_c .

The procedure for determining the correction value K_L for the spectrophotometer will now be explained. Calculation of the correction value K_L requires a correcting transmittance measuring apparatus such as described below.

Fig. 7 shows an example of the construction of a correcting transmittance measuring apparatus. In this correcting transmittance measuring apparatus 150, light (ultraviolet light) irradiated from a light source 152 is condensed by a first condensing lens 161 and then enters a diffraction grating 153 through a spectroscopy entrance slit 171. The beam which is reflected and diffracted at the diffraction grating 153 is irradiated toward a second condensing lens 162 through a spectroscopy exit slit 172, where it is again condensed and its brightness adjusted by a diaphragm 173. The

beam passing through the diaphragm 173 is shaped to a prescribed shape by a pinhole 174 and then converted to a parallel beam with a collimator lens 163 and irradiated onto a first half-mirror 181.

5 The light reflected at the first half-mirror 181 is irradiated onto an object 151 through an optical chopper 154 for the measuring beam. The transmitted beam that has passed through the object 151 is irradiated onto a detector 156 through a mirror 183, a
10 second half-mirror 184 and a condensing lens 164.

Meanwhile, the reference beam that has passed through the first half-mirror 181 is irradiated onto the second half-mirror 184 through a first mirror 182 and an optical chopper 155 for the reference beam, and the
15 reference beam reflected at the second half-mirror 184 is irradiated onto the detector 156 through the condensing lens 164. The transmitted beam and the reference beam received at the detector 156 are separated by a processor 157 and the transmitted beam
20 intensity I and reference beam intensity I_0 are determined. The ratio I/I_0 of the reference beam intensity I_0 and the transmitted beam intensity I is used to calculate the transmittance. All the members of the apparatus except for the detector 156 and the
25 processor 157 are sealed in a vacuum chamber 158 and the atmosphere surrounding the measuring beam is

adjusted to produce a nearly vacuum pressure.

By varying the slit width of the spectroscope entrance slit 171 and spectroscope exit slit 172 and the hole diameter of the pinhole 174 and moving the second condensing lens 162, the diaphragm 173, the pinhole 174 and the collimator lens 163 along the optical axis, it is possible to adjust the angle of divergence of the measuring beam at the position at which it passes through the object 151. The angle of divergence is adjusted to under 10 milliradians (0.57°). This is to reduce variation in the measuring optical path due to refraction by the object 151, thereby preventing measuring errors caused by uneven sensitivity on the reception surface of the detector 156.

The atmosphere surrounding the optical path of the measuring beam is adjusted to an approximate vacuum, i.e., a pressure of no greater than 1×10^{-2} Torr (1.33 Pa), or a pressure of no greater than 2×10^{-3} Torr (0.27 Pa) as the oxygen partial pressure. This is to reduce the effect of absorption by oxygen molecules within the differential between the optical path length of the transmitted beam and the optical path length of the reference beam due to the thickness of the object 151.

In order to determine the correction value K_L of

the spectrophotometer 110 using a correcting transmittance measuring apparatus 150 having the construction described above, first a plurality of correction samples are fabricated of the same material as the calibration sample M (i.e. the same material as the evaluation sample M) but with different thicknesses. One of the correction samples is given the same thickness as the calibration sample M (i.e. the same thickness L_0 as the evaluation sample M) (and therefore the calibration sample itself may be used). After cleaning each correction sample, the transmittance T_1 of each is measured using a correcting transmittance measuring apparatus 150 before the critical elapsed time $[t_m]$ has elapsed (i.e., within the prescribed time period). The transmittance measurement is carried out for each correction sample, with cleaning being followed by transmittance measurement, and the time elapsed during the transmittance measurement (time elapsed from completion of cleaning) is the same for all. This procedure is used because it is usually not possible to complete measurement of transmittance for all of the correction samples before the critical elapsed time $[t_m]$ has elapsed (and therefore calibration using formula (1) is not possible). The loss Y of each correction sample is determined from each transmittance T_1 obtained in this manner, using

the following formula (2).

$$Y = -\text{LN}(T_l/T_{th}) \quad (2)$$

In formula (2), T_{th} is the theoretical transmittance unique to the material of the correction sample. Once the relationship between the sample thickness L and the loss Y has been obtained using formula (2), the results are plotted on a coordinate graph with sample thickness L on the horizontal axis and loss Y on the vertical axis, to prepare a second plot graph. The plot sequence represented by the second plot graph can be fitted to a line (as shown in Fig. 8, for example). The line inclines gradually as the sample thickness L increases (i.e. it has a positive slope). The slope of the line is calculated as the internal loss coefficient β (/cm) of the correction sample.

The transmittance T_o of each correction sample is expressed by the following formula (3), using the internal loss coefficient β (/cm) and the sample thickness L (cm) obtained by the procedure described above.

$$T_o = T_{th} \times \exp(-\beta \times L) \quad (3)$$

It is assumed that the difference from the true value due to measuring error, i.e. insufficient measuring precision of the spectrophotometer 110, can be removed if the transmittance T_c at reference time t_c

obtained from formula (1) is multiplied by the correction value K_L , giving the following formula (4).

$$T_o = K_L \times T_c \quad (4)$$

5 The following formula (5) is then obtained by combining formula (3) and formula (4).

$$K_L = (T_{th}/T_c) \times \exp(-\beta \times L) \quad (5)$$

10 Here, K_L is calculated by determining the value of the transmittance T_c corresponding to the reference time t_c based on the line used earlier for fitting in the first plot graph, and plugging in the already determined internal loss coefficient β and calibration sample thickness ($= L_o$) into formula (5).

15 This calculation gives the correction value K_L for the spectrophotometer 110 corresponding to the material and thickness ($= L_o$) of the evaluation sample M.

20 Once both parameters, the transmittance reduction rate $[a]$ and critical elapsed time $[t_m]$ corresponding to the material and thickness ($= L_o$) of the evaluation sample M, and the correction value K_L for the spectrophotometer have been obtained in the manner described above, it is possible to calculate the transmittance (true transmittance T_o) for the evaluation sample M according to the first to fourth steps shown in Fig. 4. This will now be explained.

25 In order to determine the transmittance (true transmittance) T_o of the evaluation sample M, first the

evaluation sample M is cleaned (including a drying step) (first step), as shown in Fig. 4. When cleaning is completed, the evaluation sample M is placed in the spectrophotometer 110 and the transmittance is measured within the prescribed time established from the critical elapsed time [tm] which is already known from the previous process, to determine the transmittance T (second step). The cleaned evaluation sample M is placed and held in a dessicator, and removed from the dessicator only when measuring the transmittance. (The same applies when a plurality of evaluation samples are used.) Once the transmittance T has been determined, the value for the elapsed time [t] at the time of measurement of the transmittance T and the value for the transmittance reduction rate [a] are plugged into formula (1), to obtain the transmittance Tc for the reference time tc (third step). Once the standard transmittance Tc has been determined, the correction value K_L which is known from the previous process is used for correction by formula (4), to obtain the true transmittance To (fourth step).

By obtaining the true transmittance To in this manner, it is possible to calculate the internal loss coefficient β for the evaluation sample M by the following formula (6) obtained by modifying formula (3).

$$\beta = -\ln(T_o/T_{th})/L \quad (6)$$

The loss coefficient of each of the synthetic silica glass members before ultraviolet irradiation is measured by this procedure, and those with a value of no greater than 0.0020 cm^{-1} are selected.

5 The synthetic silica glass obtained in this manner having a hydrogen molecule concentration of 1×10^{16} molecules/cm³ to 2×10^{18} molecules/cm³ and a loss factor of no greater than 0.0020 cm^{-1} before ultraviolet irradiation will usually have a loss factor
10 of no greater than 0.0050 cm^{-1} at 193.4 nm as measured after irradiation with an ArF excimer laser with 1×10^4 pulse irradiation at an energy density from 0.1 $\mu\text{J}/\text{cm}^2 \cdot \text{p}$ to $200 \text{ mJ}/\text{cm}^2 \cdot \text{p}$.

15 The loss factor at 193.4 nm to be measured after irradiation is then measured during irradiation using a transmittance measuring apparatus. First, from among the synthetic silica glass members having a hydrogen molecule concentration of 1×10^{16} molecules/cm³ to 2×10^{18} molecules/cm³ and a loss factor of no greater than
20 0.0020 cm^{-1} before ultraviolet irradiation there are formed several groups, with each group consisting of glass members obtained from the same position of the ingot and having equivalent optical properties. One synthetic silica glass member is then taken from one
25 group at random and the loss coefficient at 193.4 nm is measured after irradiation with an ArF excimer laser

with 1×10^4 pulse irradiation at an energy density from $0.1 \mu\text{J}/\text{cm}^2 \cdot \text{p}$ to $200 \text{ mJ}/\text{cm}^2 \cdot \text{p}$. If the measured loss coefficient of the synthetic silica glass member at 193.4 nm is no greater than 0.0050 cm^{-1} , then the synthetic silica glass members of the same group as this synthetic silica glass member that have not been irradiated with the ArF excimer laser are selected as the synthetic silica glass members to be used in the optical system construction step described below.

Thus, synthetic silica glass members satisfying the conditions of a loss factor of no greater than 0.0020 cm^{-1} before ultraviolet irradiation and a loss factor of no greater than 0.0050 cm^{-1} at 193.4 nm are selected in the loss factor measuring step.

In the optical system constructing step, the synthetic silica glass members satisfying these conditions are used to construct at least one from among the synthetic silica glass members for the illumination optical system, the synthetic silica glass members for the projection optical system and the reticle, thereby completing the stepper 1.

Thus, since all or some of the optical members such as lenses of the stepper 1 are synthetic silica glass members with the properties described above, the transmittance of the apparatus as a whole is sufficiently high enough for practical use even when

the light source 11 has a short wavelength of under 200 nm such as is typical of an ArF excimer laser.

Needless to mention, high transmittance sufficient for practical use is guaranteed even if the light source 11
5 of the stepper is replaced with one that irradiates light of a longer wavelength than an ArF excimer laser.

The present invention will now be explained in greater detail by way of the following examples and comparative examples, with the understanding that the
10 invention is in no way limited to these examples.

First, the aforementioned synthetic silica glass production apparatus 50 was used to produce five different synthetic silica glass ingots, varying the synthesis conditions such as the raw material flow and
15 the oxygen gas/hydrogen gas flow ratio. The shape of the ingot is usually 180 ϕ to 620 ϕ (ϕ : diameter in mm) x 600-1200 t (t: thickness in mm), and heat treatment is generally carried out with the ingot cut into a block shape with t of 50-300 mm perpendicular to the
20 direction of growth.

As the heat treatment conditions, the ingots were held at 1000°C for 10 hours, the temperature was then lowered to below 500°C at a temperature lowering rate of no more than 10°C/hour, and they were subsequently
25 allowed to cool. A lump with a shape of $\phi = 60$ mm, thickness = 10 mm is then cut out from each ingot and

subjected to fine polishing to obtain 12 evaluation samples (synthetic silica glass members).

After calculating the transmittance of each of these 12 evaluation samples before irradiation according to the method described above, the average hydrogen molecule concentration of each sample was measured by Raman spectroscopy. Specifically, the Raman scattering intensity at 800 cm^{-1} and 4135 cm^{-1} was measured according to V.S. Khotimchenko et al., J. Appl. Spectrosc., 46, 632-635(1987), and the luminous intensity was determined. An ArF excimer laser was then used for 1×10^4 pulse irradiation at various energy density values between $0.1\text{ }\mu\text{J}/\text{cm}^2\cdot\text{p}$ and $200\text{ mJ}/\text{cm}^2\cdot\text{p}$, and the transmittance at 193.4 nm wavelength after irradiation was determined. After determining the transmittance for each sample, formula (6) was used to calculate the loss coefficients of the samples after ArF excimer laser irradiation. The theoretical transmittance used for formula (6) was $90.8748(\%)$, as the value for synthetic silica glass at 193.4 nm wavelength.

For some of the samples (Examples 5 and 9), the variation width V of the hydrogen molecule concentration values of the samples in the radial direction, as explained above, was also determined.

The loss coefficients of the 12 evaluation samples

before and after ArF excimer laser irradiation were calculated. The results are shown in Table 1. Nine of the 12 evaluation samples which satisfied the conditions of a loss factor of no greater than 0.0020 cm^{-1} before ultraviolet irradiation and an average loss factor of no greater than 0.0050 cm^{-1} after irradiation at 193.4 nm are listed in Table 1 as Examples 1 to 9. The remaining three evaluation samples that did not satisfy these conditions are listed in Table 1 as Comparative Examples 1 to 3.

Fig. 9 shows variation in the loss factor with respect to the irradiation pulse number for irradiation of Example 5 and Comparative Example 1 with an ArF excimer laser at an energy density of 2 $\text{mJ}/\text{cm}^2 \cdot \text{p}$. Fig. 10 shows variation in the loss factor with respect to the irradiation pulse number for irradiation of Example 8 and Comparative Example 3 with an ArF excimer laser at an energy density of 200 $\text{mJ}/\text{cm}^2 \cdot \text{p}$.

Table 1

	Raw material flow (g/min)	(Oxygen gas)/(Hydrogen gas) flow ratio	Heat treatment	Loss factor before irradiation (/cm ⁻¹)	Average hydrogen concentration (molecules/cm ³)	ArF irradiation energy density (mJ/cm ² ·p)	Average loss factor after irradiation [initial irradiation absorption] (/cm ⁻¹)	Score
Example 1	30	0.385	yes	0.0016	1.6×10^{18}	0.2	0.00078	4
Example 2	30	0.385	yes	0.0013	1.6×10^{18}	0.5	0.0018	4
Example 3	30	0.382	yes	0.0015	1.1×10^{18}	0.7	0.0014	4
Example 4	30	0.385	yes	0.0011	1.6×10^{18}	1	0.0025	4
Example 5	30	0.378	yes	0.0016	1.8×10^{18} [variation width V: -20%SV±20%]	2	0.0025 {0.0022-0.0032}	4
Example 6	30	0.385	yes	0.0014	1.6×10^{18}	10	0.005	4
Example 7	30	0.386	yes	0.0014	1.5×10^{18}	100	0.0025	4
Example 8	30	0.388	yes	0.0012	9.8×10^{17}	200	0.0025	4
Example 9	30	0.378	yes	0.0016	1.8×10^{18} [variation width V: -60%SV±60%]	2	0.005 {0.0075-0.0010}	3
Comp. Ex. 1	45	0.246	no	0.0043	5×10^{18}	2	0.0142	0
Comp. Ex. 2	45	0.246	yes	0.0047	5×10^{18}	200	0.0057	0
Comp. Ex. 3	60	0.355	no	0.0011	6×10^{18}	200	0.0375	1

From Table 1 it was confirmed that for all of the samples having a hydrogen molecule concentration of 1×10^{16} molecules/cm³ to 2×10^{18} molecules/cm³ and a loss factor of no greater than 0.0020 cm⁻¹ before
5 ultraviolet irradiation, the variation width V of the hydrogen molecule concentration was in the range of -50% $\leq V \leq$ + 50%, and the loss factors after irradiation with the ArF excimer laser were no greater than 0.005 cm⁻¹.

10 When a plurality of samples having hydrogen molecule concentrations and loss factors before and after irradiation that were equivalent to those exhibited by the examples were mounted at synthetic silica glass sections of the illumination optical
15 system and projection optical system of a stepper having the same construction as the aforementioned stepper 1, the necessary resolution of 0.13 μ m was obtained, thus confirming satisfactory performance for practical use.

20 It was also judged whether or not the stepper exhibits satisfactory performance for practical use. One point was assigned for a hydrogen molecule concentration of 1×10^{16} molecules/cm³ to 2×10^{18} molecules/cm³, one point was assigned for a hydrogen
25 molecule concentration value variation width V in the range of -50% $\leq V \leq$ +50%, one point was assigned for a

loss factor of no greater than 0.0020 cm^{-1} before ultraviolet irradiation and one point was assigned for an average loss factor at 193.4 nm of no greater than 0.0050 cm^{-1} after 1×10^4 pulse irradiation with an ArF excimer laser, and the total points were summed. The results of the total sum are shown in Table 1. A stepper with a total sum of three or more points exhibits satisfactory performance for practical use as a stepper. The hydrogen molecule concentration value variation widths V of the samples of Examples 1 to 8 (all except Example 9) were in the range of $-50\% \leq V \leq +50\%$. The hydrogen molecule concentration value variation widths V of the samples of Comparative Examples 1 to 3 were all in a range larger than the range of $-50\% \leq V \leq +50\%$.

As confirmed by this mounting in steppers, Examples 1 to 9 which had loss factors (initial irradiation absorption) of no greater than 0.0050 cm^{-1} after ArF excimer laser irradiation at 1×10^4 pulses exhibited performance suitable for practical use, while Comparative Examples 1 to 3 which had loss factors of greater than 0.0050 cm^{-1} after ArF excimer laser irradiation did not exhibit performance suitable for practical use. It was confirmed that those with an average hydrogen molecule concentration of $5 \times 10^{18}/\text{cm}^3$ or greater as in Comparative Example 3 have a large

hydrogen molecule concentration value variation width and a very large loss coefficient after 1×10^4 pulse irradiation with an ArF excimer laser.

5 The hydrogen molecule concentration values of the sample of Example 5 in the radial direction were distributed in a narrow range of $1.4 \times 10^{18} - 2.2 \times 10^{18}$ molecules/cm³, and the hydrogen molecule concentration value variation width V was $-20\% \leq V \leq +20\%$. The hydrogen molecule concentration values of the sample of
10 Example 9 in the radial direction were distributed in a narrow range within $0.76 \times 10^{18} - 2.9 \times 10^{18}$ molecules/cm³, and the hydrogen molecule concentration value variation width V was $-60\% \leq V \leq +60\%$.

Industrial Applicability

15 As explained above, the synthetic silica glass members of the invention have properties such that, upon 1×10^4 pulse irradiation with an ArF excimer laser at an energy density from $0.1 \mu\text{J}/\text{cm}^2 \cdot \text{p}$ to $200 \text{ mJ}/\text{cm}^2 \cdot \text{p}$, the loss factor at 193.4 nm measured after
20 irradiation is no greater than 0.0050 cm^{-1} , and by using such synthetic silica glass for construction of all or some of the optical members of a photolithography apparatus it is possible to increase the transmittance of the photolithography apparatus to
25 exhibit adequate performance for practical use even when the light source used is an ArF excimer laser.

CLAIMS

1. A synthetic silica glass member for use in a photolithography apparatus employing light in a wavelength range of 400 nm or less, wherein

said glass member is selected from any one among the glass members which are adjusted to have a hydrogen molecule concentration being from 1×10^{16} molecules/cm³ to 2×10^{18} molecules/cm³ by adjusting the synthesis and/or heat treatment conditions of a synthetic silica glass ingot which is a source material,

wherein said glass member having a loss factor which satisfies the following condition represented by formula (i) and (ii)

$$A \leq 0.0020 \text{ cm}^{-1} \quad (i)$$

$$B \leq 0.0050 \text{ cm}^{-1} \quad (ii)$$

[In formula (i) and (ii), A represents a loss factor before ultraviolet irradiation, B represents a loss factor at 193.4 nm measured after 1×10^4 pulse irradiation with an ArF excimer laser at an energy density from 0.1 $\mu\text{J}/\text{cm}^2 \cdot \text{p}$ to 200 $\text{mJ}/\text{cm}^2 \cdot \text{p}$.]

2. A photolithography apparatus comprising an exposure light source that emits light with a wavelength of 400 nm or less as the exposure light, a reticle with a pattern image formed therein, an illumination optical system that irradiates light outputted from said exposure light source onto said

reticle, a projection optical system that projects the pattern image outputted from said reticle onto a photosensitive plate and an alignment system that positions said reticle and said photosensitive plate,

5 wherein at least some of the synthetic silica glass members composing said illumination optical system, the synthetic silica glass members composing said projection optical system and said reticle consist of synthetic silica glass members according to claim 1.

10 3. A process for producing a photolithography apparatus which comprises an exposure light source that emits light with a wavelength of 400 nm or less as the exposure light, a reticle with a pattern image formed therein, an illumination optical system that irradiates
15 light outputted from said exposure light source onto said reticle, a projection optical system that projects the pattern image outputted from said reticle onto a photosensitive plate and an alignment system that positions said reticle and said photosensitive plate,
20 the process comprising

 an ingot synthesizing step in which a synthetic silica glass ingot with a hydrogen molecule concentration of from 1×10^{16} molecules/cm³ to 2×10^{18} molecules/cm³ is synthesized,

25 an ingot cutting step in which said synthetic silica glass ingot is cut to obtain a synthetic silica glass member of the prescribed shape and size,

a loss factor measuring step for measurement of the loss factor of said synthetic silica glass member before ultraviolet irradiation and the loss factor at 193.4 nm after irradiation with an ArF excimer laser with 1×10^4 pulse irradiation at an energy density from $0.1 \mu\text{J}/\text{cm}^2 \cdot \text{p}$ to $200 \text{ mJ}/\text{cm}^2 \cdot \text{p}$, to obtain a synthetic silica glass member with a loss factor of no greater than 0.0020 cm^{-1} before said ultraviolet irradiation and a loss factor of no greater than 0.0050 cm^{-1} at 193.4 nm, and

an optical system constructing step in which the synthetic silica glass member obtained in said loss factor measuring step is used to construct at least some of the synthetic silica glass members composing said illumination optical system, the synthetic silica glass members composing said projection optical system and said reticle.